

**ROCHESTER INSTITUTE OF TECHNOLOGY
MICROELECTRONIC ENGINEERING**

Evaluation of Pressure Sensor Performance

Dr. Lynn Fuller

Webpage: <http://people.rit.edu/lffeee>

Microelectronic Engineering

Rochester Institute of Technology

82 Lomb Memorial Drive

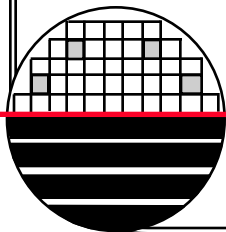
Rochester, NY 14623-5604

Tel (585) 475-2035

Fax (585) 475-5041

Email: Lynn.Fuller@rit.edu

Department webpage: <http://www.microe.rit.edu>



OUTLINE

Introduction

Theory

SEM Pictures

Basics

Response

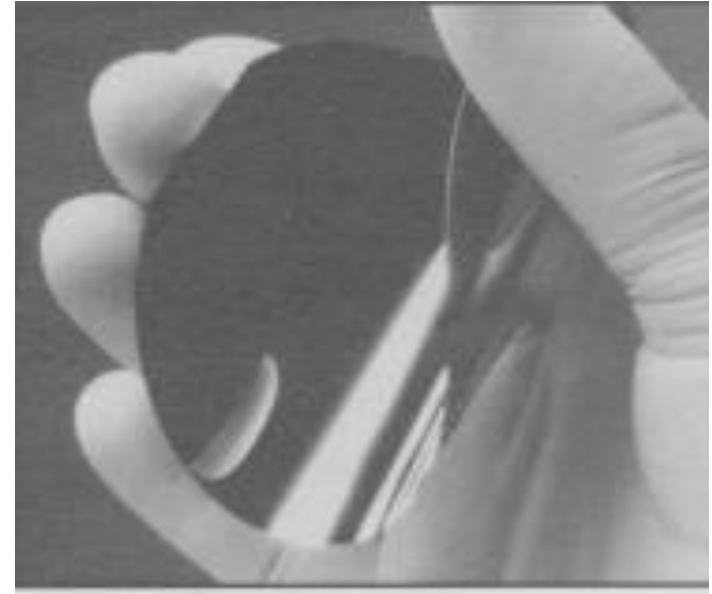
Offset, Span, Linearity, etc.

Compensation

Temperature Dependence and Compensation

Frequency Response

References



Thickness = 10 μm
Diameter 75 mm

INTRODUCTION

In this lab we will test piezoresistive pressure sensors made at RIT and compare them with sensors made by Freescale Semiconductor

PIN NUMBER			
1	Gnd	3	V _s
2	+V _{out}	4	-V _{out}

NOTE: Pin 1 is noted by the notch in the lead.



MOTOROLA Freescale Semiconductor, Inc. SEMICONDUCTOR TECHNICAL DATA

10 kPa On-Chip Temperature Compensated & Calibrated Silicon Pressure Sensors

The MPX2010/MPXV2010G series silicon piezoresistive pressure sensors provide a very accurate and linear voltage output — directly proportional to the applied pressure. These sensors house a single monolithic silicon die with the strain gauge and thin-film resistor network integrated on each chip. The sensor is laser trimmed for precise span, offset calibration and temperature compensation.

Features

- Temperature Compensated over 0°C to +85°C
- Ratiometric to Supply Voltage
- Differential and Gauge Options

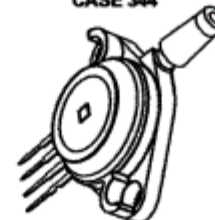
Application Examples

- Respiratory Diagnostics
- Air Movement Control
- Controllers

UNIBODY PACKAGE



MPX2010D
CASE 344



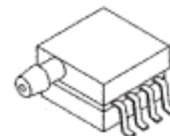
MPX2010GP
CASE 344B

MPX2010 MPXV2010G SERIES

Motorola Preferred Device

COMPENSATED
PRESSURE SENSOR
0 to 10 kPa (0 to 1.45 psi)
FULL SCALE SPAN: 25 mV

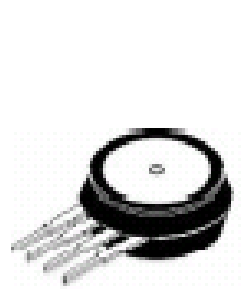
SMALL OUTLINE PACKAGE
SURFACE MOUNT



MPXV2010GP
CASE 1369

FREESCALE MPX2202 SERIES PRESSURE SENSORS

UNIBODY PACKAGES



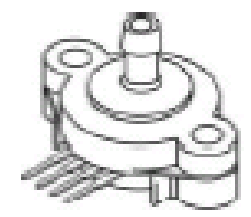
**MPX2202A
CASE 344-15**



**MPX2202APIGP
CASE 344B-01**



**MPX2202DP
CASE 344C-01**

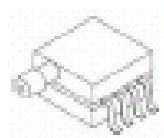


**MPX2202ASX
CASE 344F-01**

SMALL OUTLINE PACKAGES



**MPXV2202GP
CASE 1351-01**



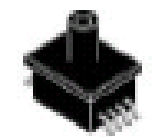
**MPXV2202GP
CASE 1369-01**



**MPXV2202GP
CASE 482A-01**

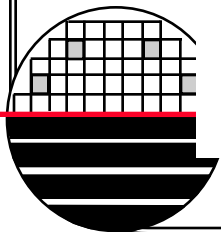


**MPXM2202A
CASE 1320-02**

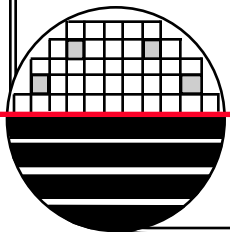
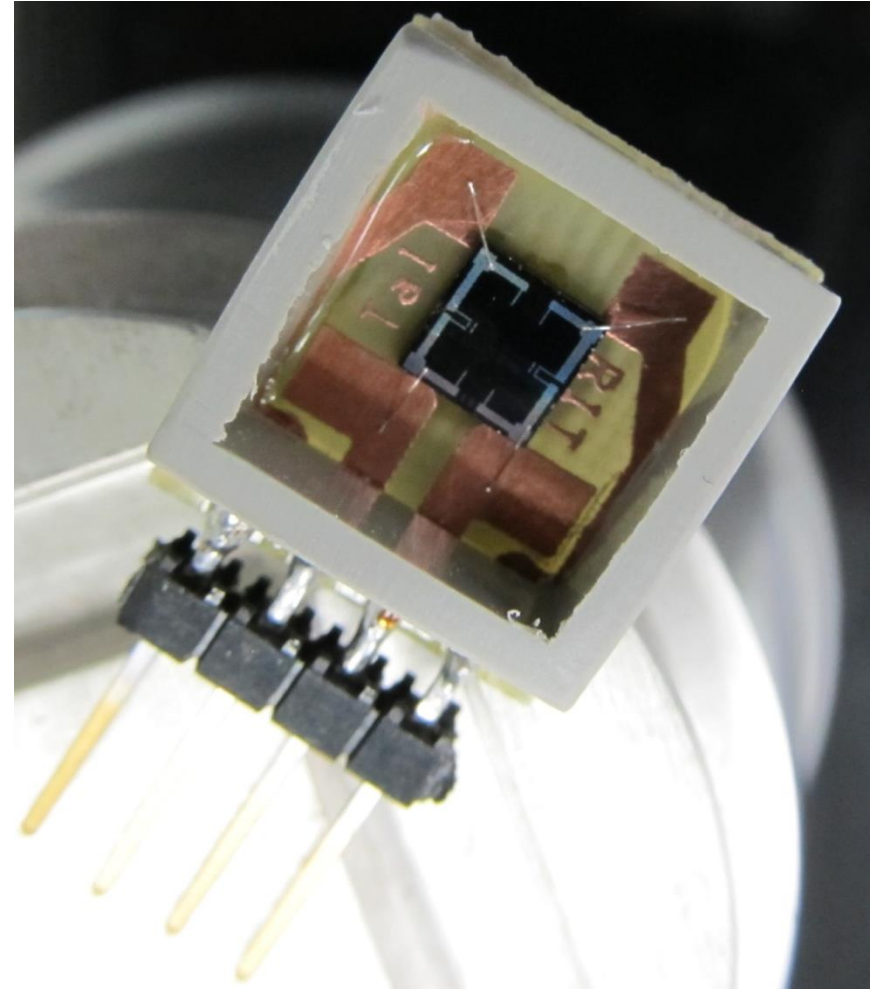
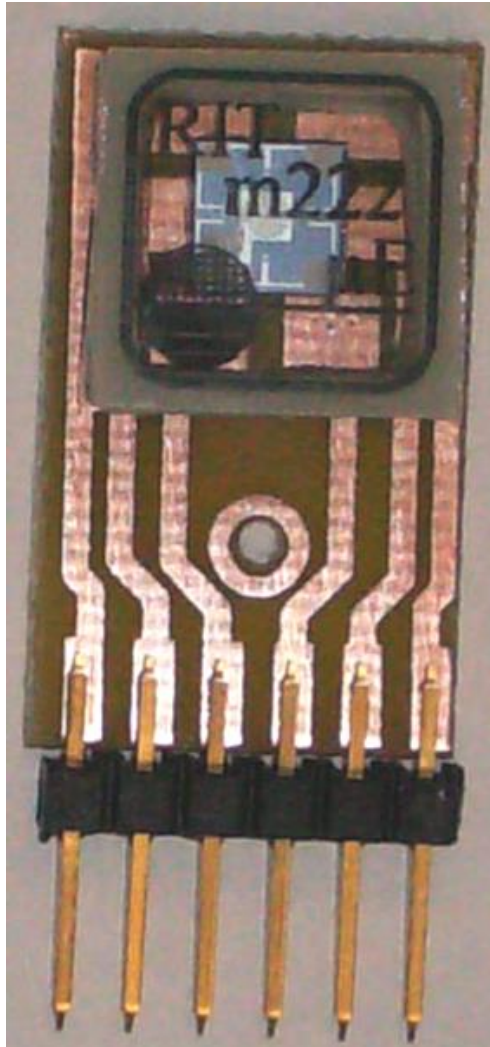
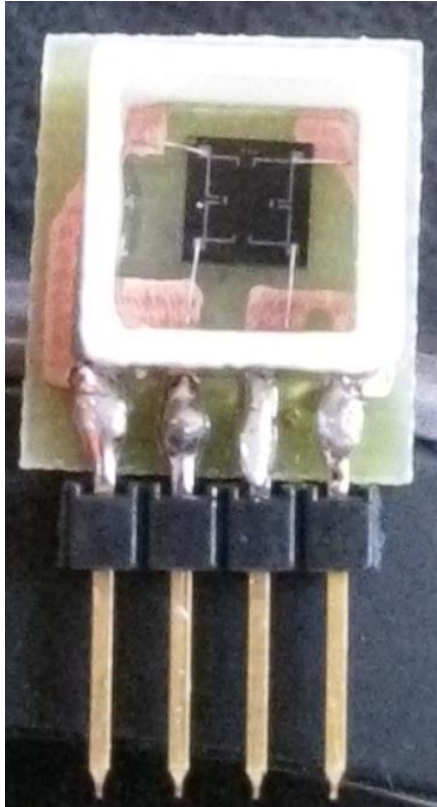


**MPXM2202GS/AS
CASE 1320A-02**

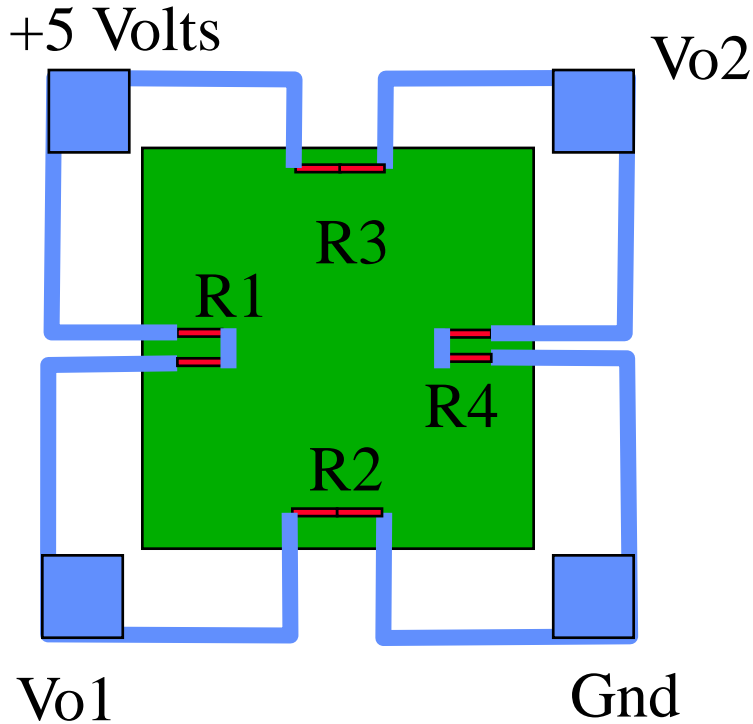
MPAK



RIT PRESSURE SENSORS



CALCULATION OF EXPECTED OUTPUT VOLTAGE



The equation for stress at the center edge of a square diaphragm (S.K. Clark and K. Wise, 1979)

Stress = $0.3 P(L/H)^2$ where P is pressure, L is length of diaphragm edge, H is diaphragm thickness

For a $3000\mu\text{m}$ opening on the back of the wafer the diaphragm edge length L is $3000 - 2(500/\text{Tan } 54.74^\circ) = 2290\mu\text{m}$

CALCULATION OF EXPECTED OUTPUT VOLTAGE (Cont.)

$$\text{Stress} = 0.3 P (L/H)^2$$

If we apply vacuum to the back of the wafer that is equivalent to and applied pressure of 14.7 psi or 103 N/m²

$$P = 103 \text{ N/m}^2$$

$$L = 2290 \text{ } \mu\text{m}$$

$$H = 25 \text{ } \mu\text{m}$$

$$\text{Stress} = 2.49\text{E}8 \text{ N/m}^2$$

Hooke's Law: Stress = E Strain where E is Young's Modulus

$$\sigma = E \varepsilon$$

Young's Modulus of silicon is 1.9E11 N/m²

Thus the strain = 1.31E-3 or .131%

CALCULATION OF EXPECTED OUTPUT VOLTAGE (Cont.)

The sheet resistance (R_{hos}) from 4 point probe is 61 ohms/sq

The resistance is $R = R_{hos} L/W$

For a resistor R_3 of $L=350 \mu\text{m}$ and $W=50 \mu\text{m}$ we find:

$$R_3 = 61 (350/50) = 427.0 \text{ ohms}$$

R_3 and R_2 decrease as W increases due to the strain

assume L is does not change, W' becomes $50+50 \times 0.131\%$

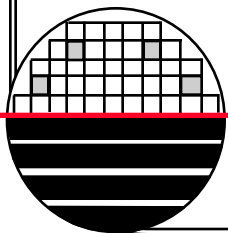
$$W' = 50.0655 \mu\text{m}$$

$$R_3' = R_{hos} L/W' = 61 (350/50.0655) = 426.4 \text{ ohms}$$

R_1 and R_4 increase as L increases due to the strain

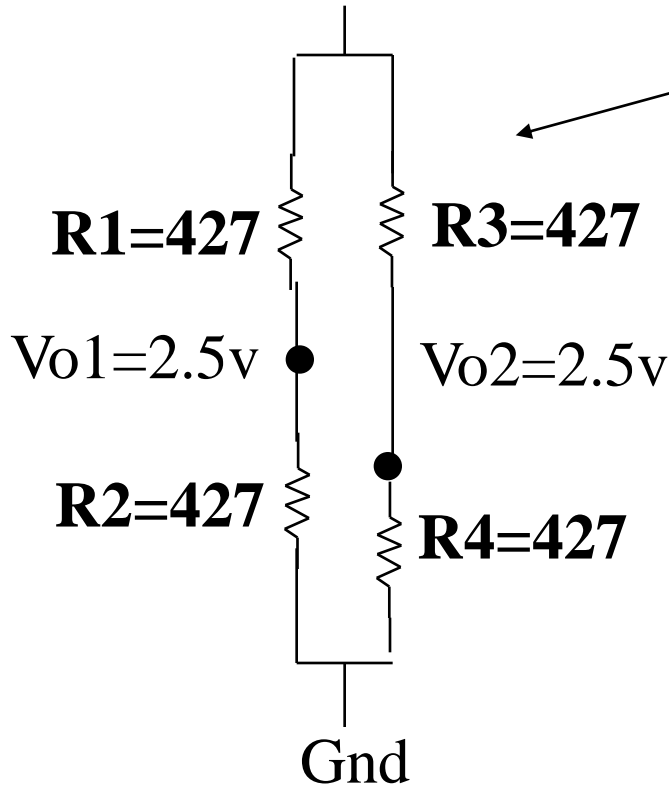
assume W does not change, L' becomes $350 + 350 \times 0.131\%$

$$R_1' = R_{hos} L'/W = 61 (350.459/50) = 427.6 \text{ ohms}$$



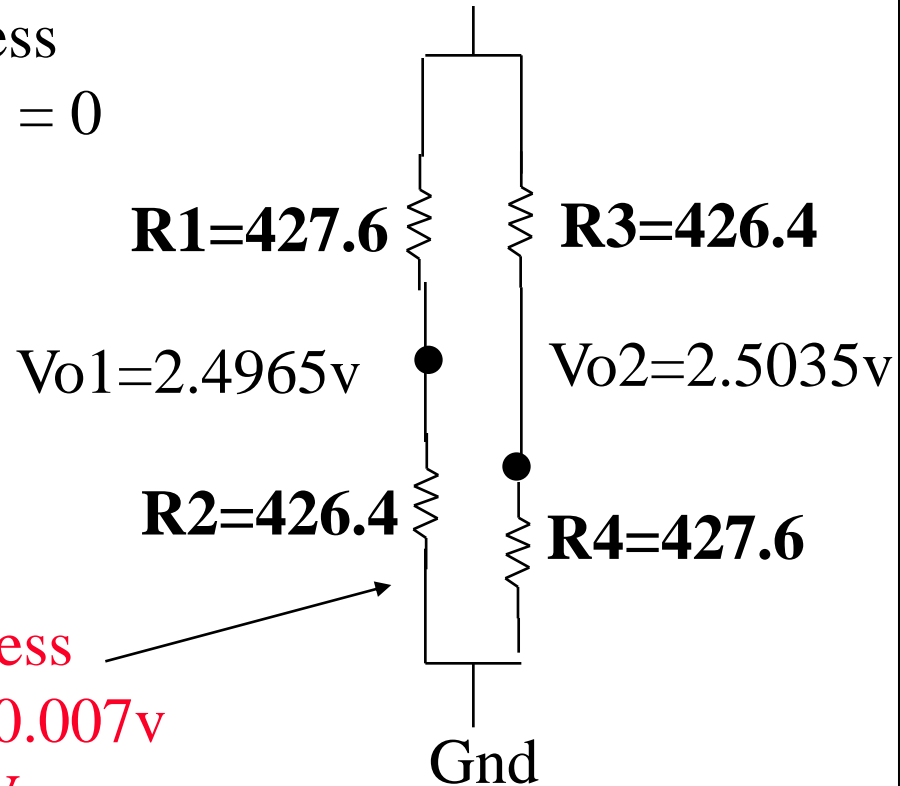
CALCULATION OF EXPECTED OUTPUT VOLTAGE (Cont.)

5 Volts

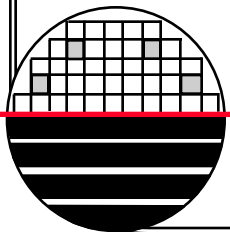


No stress
 $V_{o2}-V_{o1} = 0$

5 Volts



With stress
 $V_{o2}-V_{o1} = 0.007v$
 $= 7 \text{ mV}$



IF RESISTORS ARE SINGLE CRYSTAL SILICON

In addition to the effects of strain on the resistance if the resistor is made of single crystal silicon there is also a significant piezoresistive effect on the resistor value. Strain affects the mobility of holes and electrons in silicon. The resistors on the diaphragm of the pressure sensor drawn above have current flow longitudinal (R1 and R4) and transverse (R2 and R3) to the strain. The strain is tensile on the top surface of the diaphragm where the resistors are located if positive pressure is applied to the top of the diaphragm. The piezoresistive coefficient for R1 and R4 is 71.8 and for R2 and R3 is -66.3 E-11/Pa . The calculations above give the stress as $2.49\text{E}8 \text{ Pa}$ thus the hole mobility will decrease in R1 and R4 (R increases in value) by $2.49\text{E}8 \times 71.8\text{e-11} = 17.9\%$ while R2 and R3 (decrease in value) because the mobility increases by $2.49\text{E}8 \times 66.3\text{E-11} = 16.5\%$, thus the overall effect will be dominated by the piezoresistance rather than the effect of strain on the dimensions.

EXPRESSION FOR RESISTANCE

$$R = R_0 [1 + \pi_L \sigma_{xx} + \pi_T (\sigma_{yy} + \sigma_{zz})]$$

where $R_0 = (L/W)(1/(q\mu(N,T) Dose))$

π_L is longitudinal piezoresistive coefficient

π_T is transverse piezoresistive coefficient

σ_{xx} is the x directed stress, same direction as current

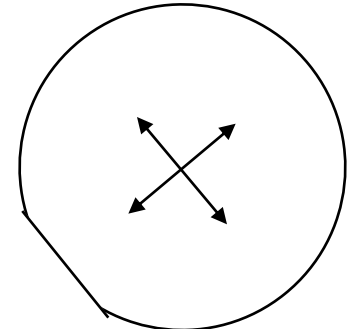
σ_{yy} is the y directed stress, transverse to current flow

σ_{zz} is the z directed stress, transverse to current flow

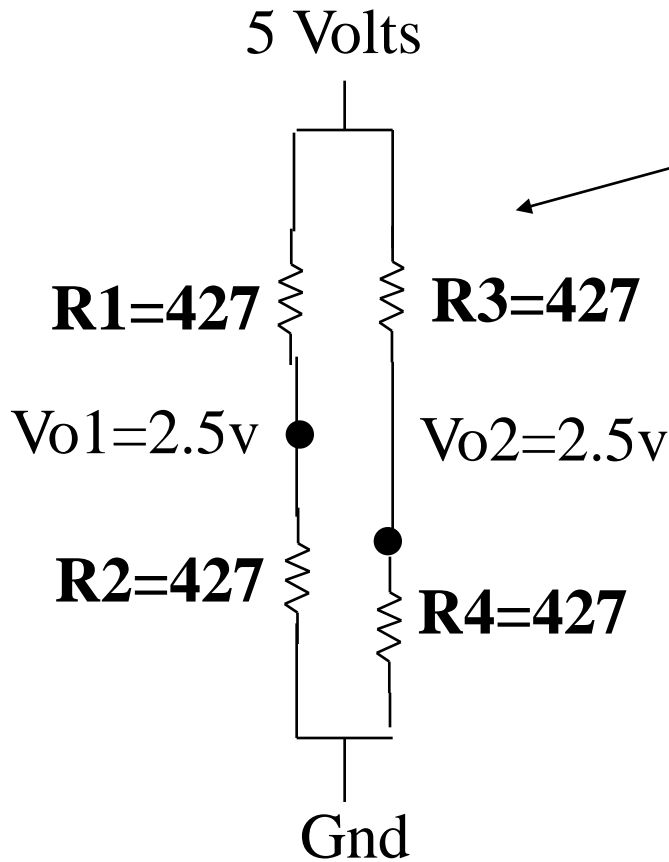
In the $\langle 110 \rangle$ direction

	π_L (E ⁻¹¹ /Pa)	π_T (E ⁻¹¹ /Pa)
Electrons	-31.6	-17.6
holes	71.8	-66.3

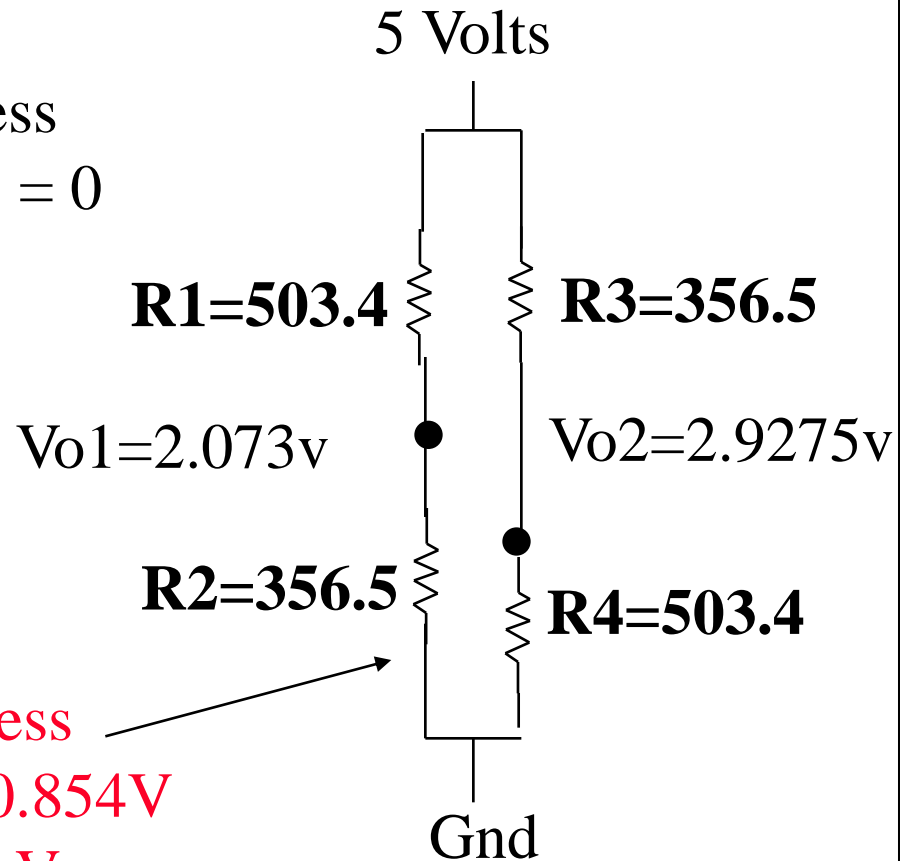
(100) wafer
 $\langle 110 \rangle$ directions



CALCULATION OF EXPECTED OUTPUT VOLTAGE FOR SINGLE CRYSTAL RESISTORS

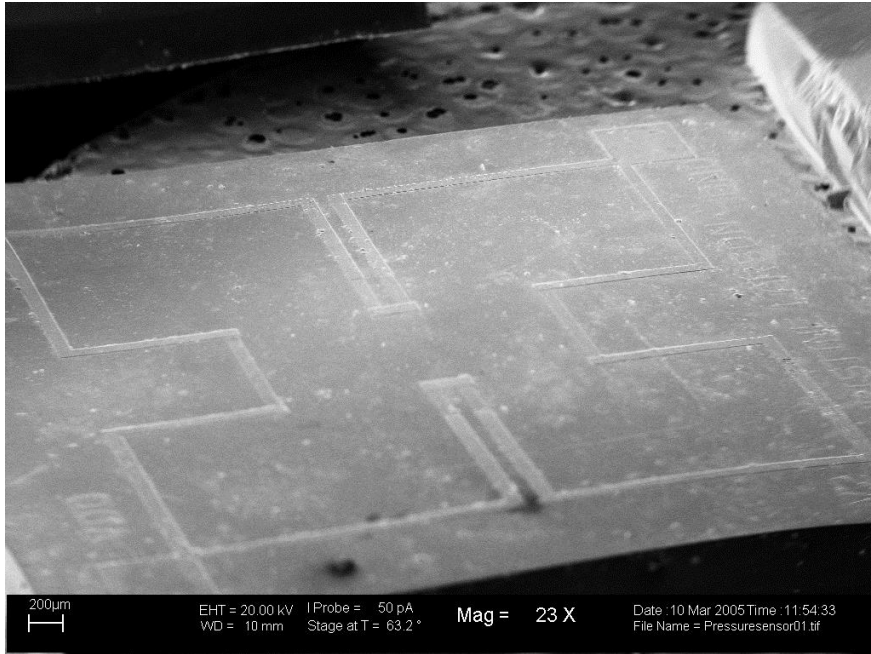


No stress
 $V_{o2}-V_{o1} = 0$

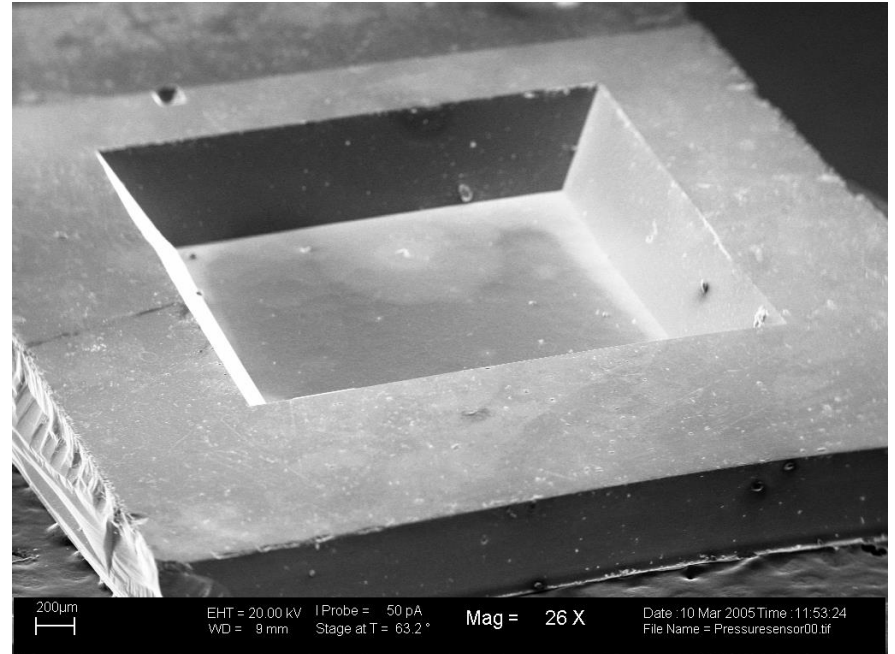


With stress
 $V_{o2}-V_{o1} = 0.854V$
 $= 854 mV$

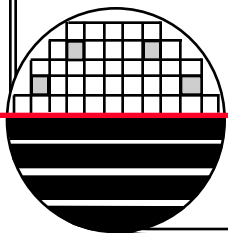
SEM OF RIT PRESSURE SENSOR



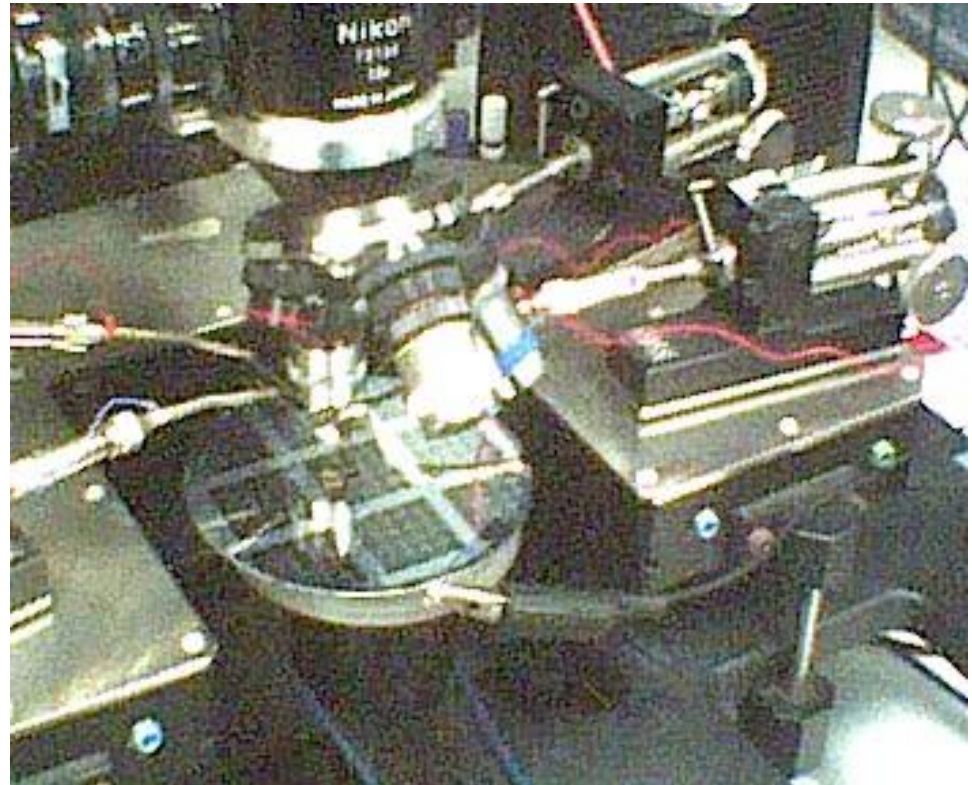
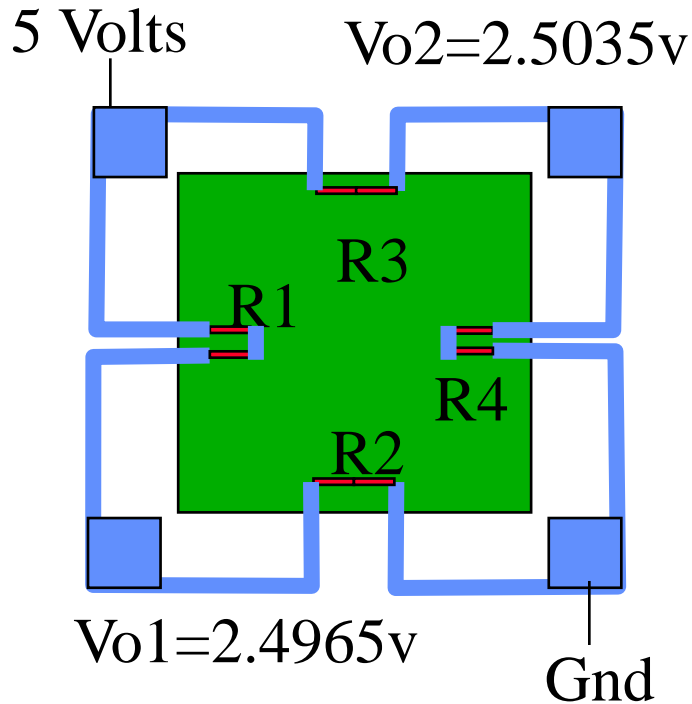
Front



Back



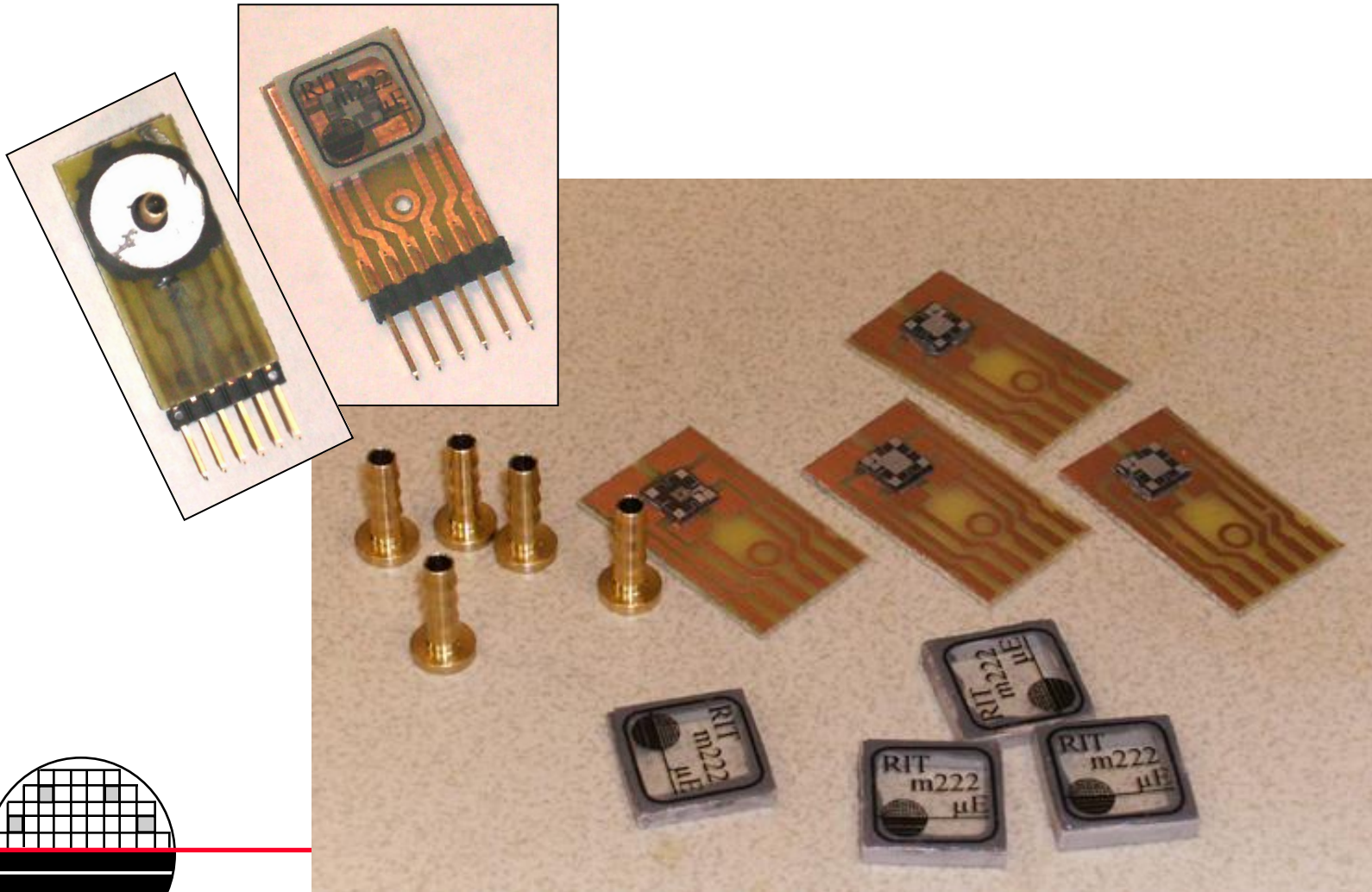
BASICS



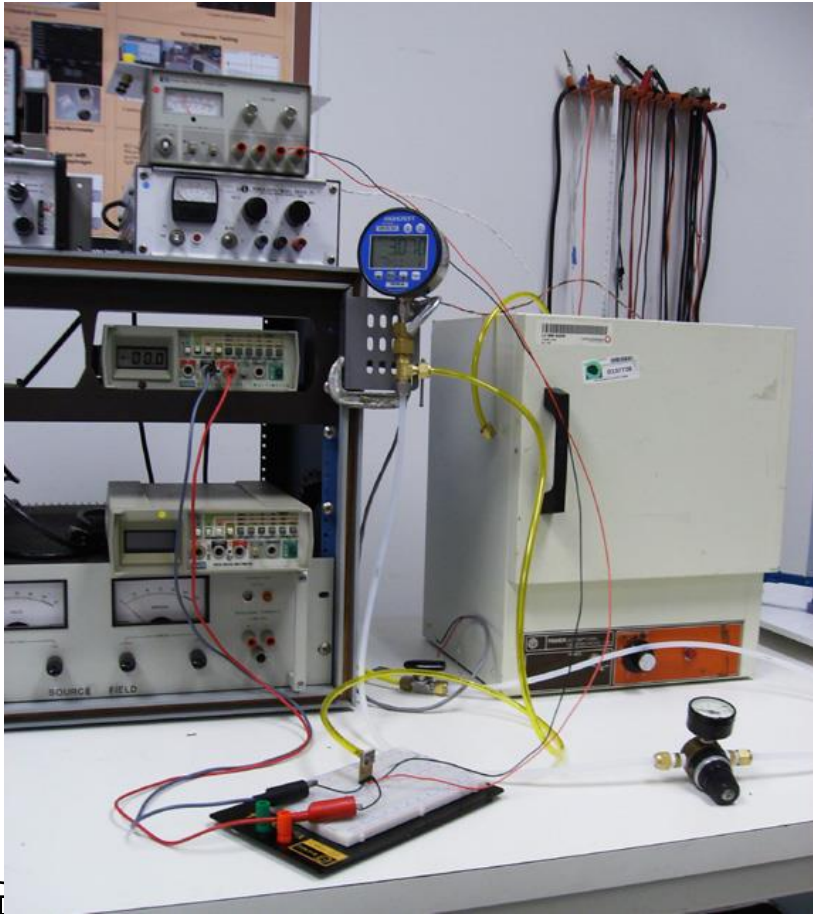
Check that v_{o1} and V_{o2} are near $V_{supply}/2$ and $V_o \sim 0$

Apply and release chuck vacuum to observe change in output voltage

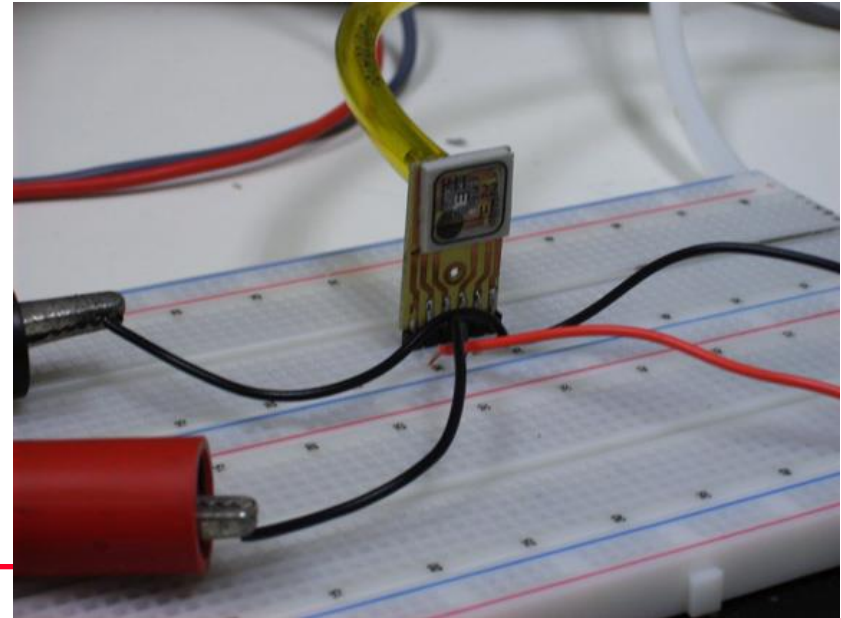
PRESSURE SENSOR PACKAGING



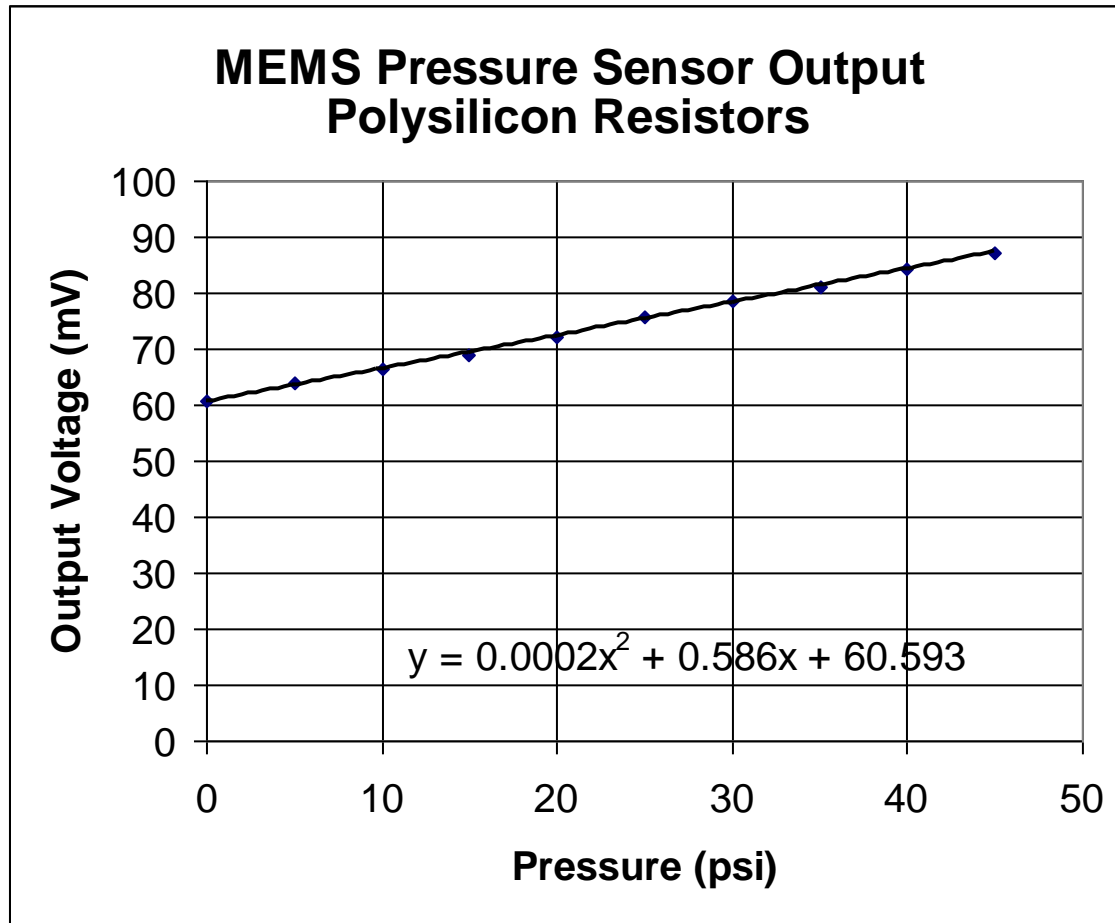
PRESSURE SENSOR TEST SETUP



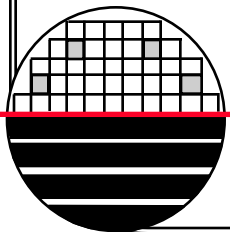
Apply pressure, measure and compare with other pressure gages. Collect data.



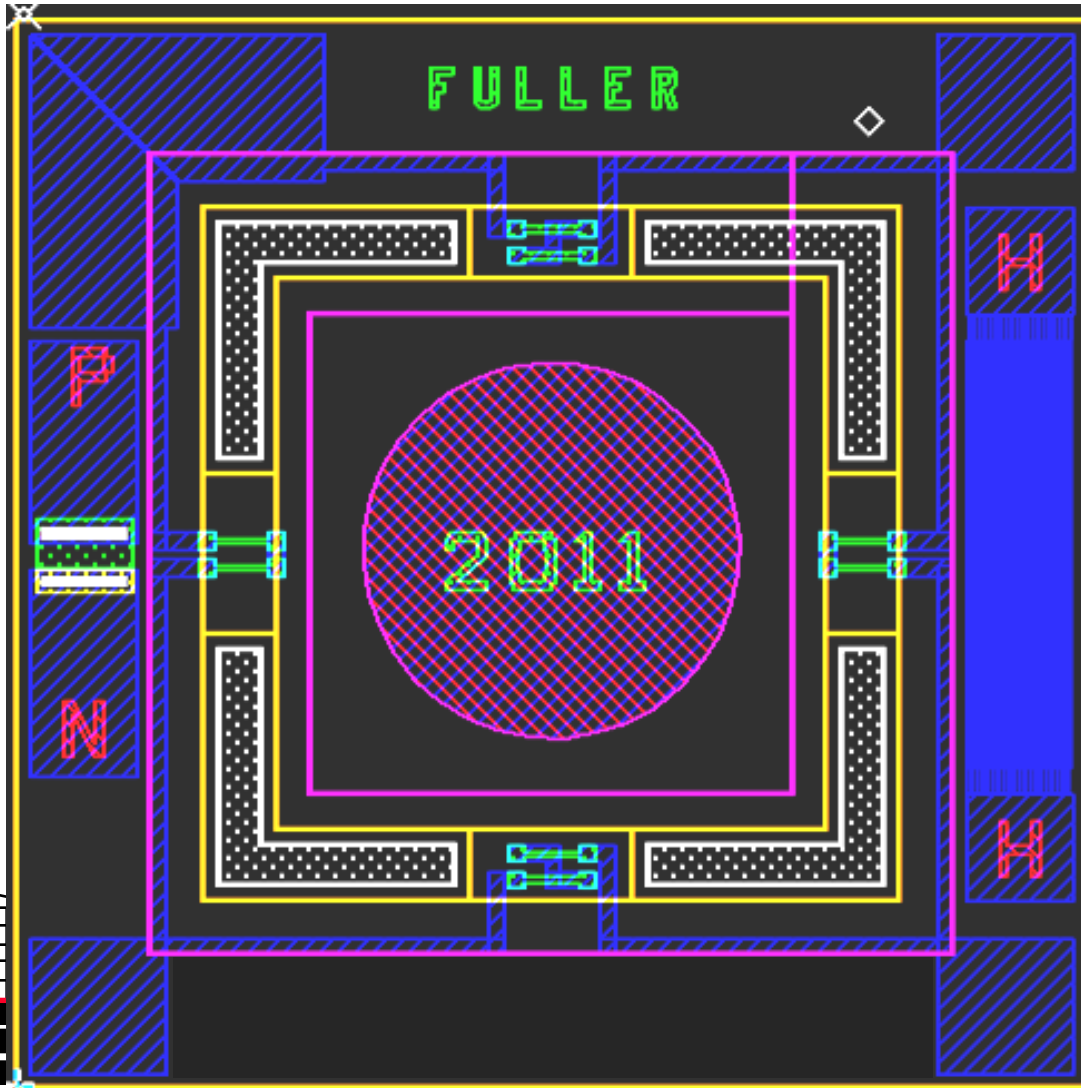
OUTPUT VOLTAGE VERSUS PRESSURE



psi	mV
0	60.6
5	63.84
10	66.32
15	68.95
20	72.28
25	75.62
30	78.68
35	81.25
40	84.39
45	87.21



PRESSURE SENSOR CHIP – VER 3



Pressure Sensor
Temperature Sensor
Humidity Sensor

Diffused Resistors

Length =

Width =

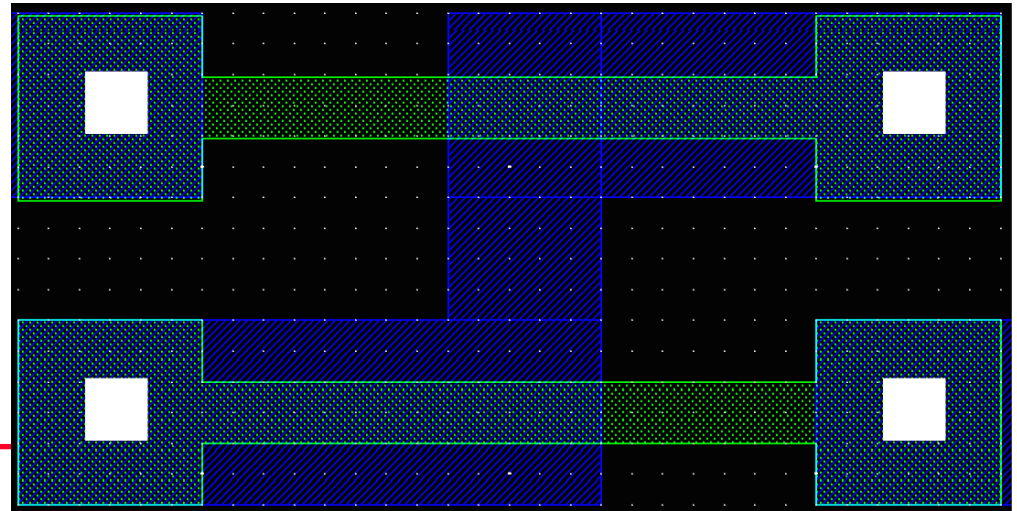
Note: upper left is not connected so individual resistances can be measured.

ELECTRICAL MEASUREMENTS

Measured resistance: $R_{top} = 3.538 \text{ Kohm}$
 $R_{right} = 3.537 \text{ Kohm}$
 $R_{bottom} = 3.537 \text{ Kohm}$
 $R_{left} = 3.537 \text{ Kohm}$

Measured Voltages: $V_{o1} = 2.535 \text{ V}$
 $V_{o2} = 2.504 \text{ V}$
 $V_{o1} - V_{o2} = 31.0 \text{ mV}$

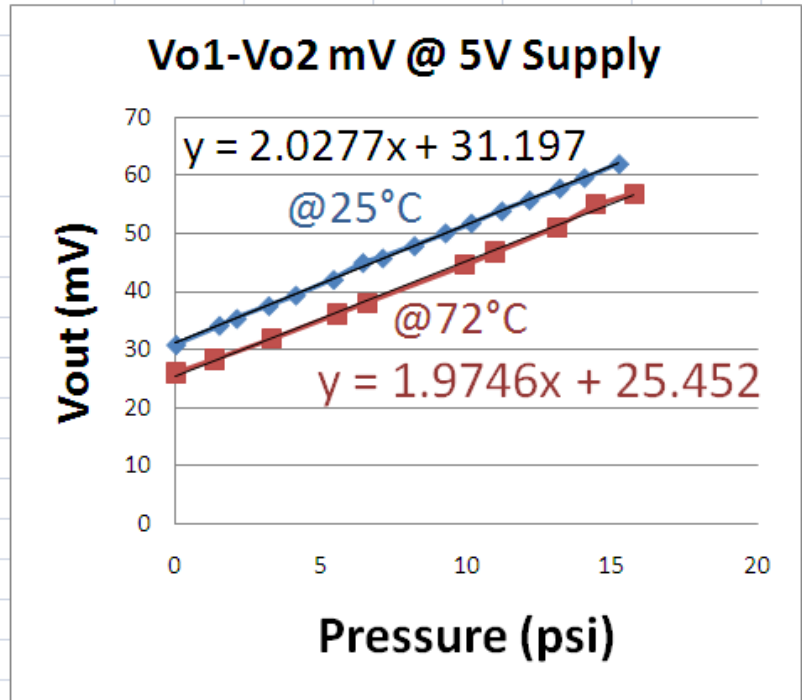
$R_{hos} \approx 150 \text{ ohm/sq}$



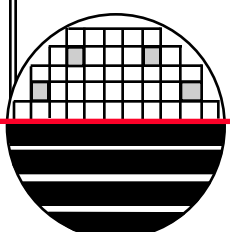
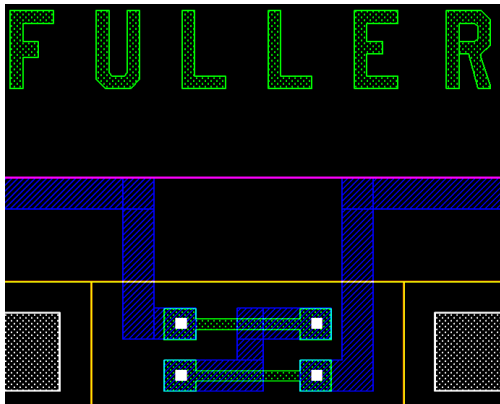
OUTPUT VOLTAGE VS PRESSURE

Diffused Resistor Pressure Sensor at 5 Volts Bias

Pressure psi	Vo1-Vo2 mV	Pressure psi	V01-V02 @72°C mV
0	30.9	0	26
1.49	34.2	1.33	28.3
2.09	35.4	3.3	31.9
3.19	37.6	5.55	36.1
4.12	39.4	6.6	38.1
5.42	42.1	9.95	44.6
6.43	45	11	46.8
7.11	45.8	13.12	51
8.2	47.9	14.45	55
9.27	50.1	15.77	56.8
10.16	51.8		
11.21	53.9		
12.16	55.75		
13.2	57.8		
14.05	59.6		
15.24	62		



Sensitivity = 0.406mV/psi/V
 or 0.0589 mV/KPa/V
 or 0.589 mV/KPa @ 10VDC



ZERO AND SPAN COMPENSATION

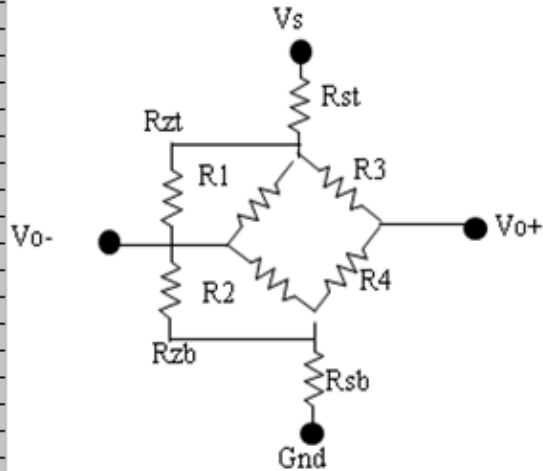
Rochester Institute of Technology
Microelectronic Engineering

Dr. Lynn Fuller
Bridge_Balance.xls

4/5/2012

This spread sheet can be used to find resistor values used to compensate a wheatstone bridge resistor pressure sensor for output offset voltage and span. If we assume that the resistors are TaN thin film resistors that are adjusted by laser trimming then the trimmed value has to be higher than the nominal value. First adjust the value of Rzt and Rzb to set Vout trimmed to zero. Then set Rst and Rsb to make the trimmed stressed value equal to the specified output voltage at maximum applied pressure.

The numbers in the white cells can be changed. The other cells in blue are calculated results.

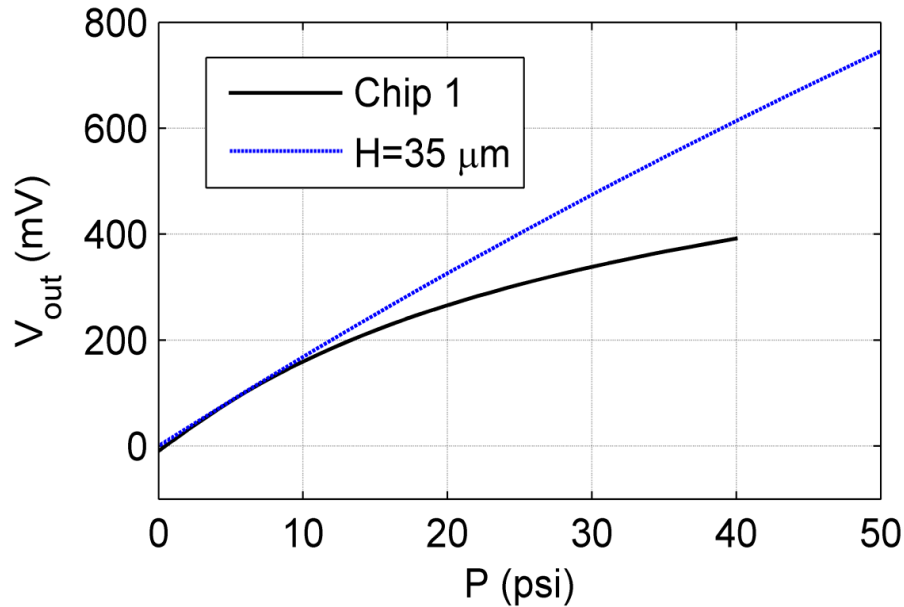


Voltage Supply		Vs=	10	Volts
Resistance of Bridge Measured with ohm meter from internal top node to internal bottom node with compensation resistors attached, or the nominal value of R1 = R2 = R3 = R4				
	Nominal R1 = R2 = R3 = R4 =	1000	ohms	
	Nominal starting value of Rzt = Rzb =	10000	ohms	
	Nominal starting value of Rst = Rsb =	100	ohms	
	Measured value of Vo+ =	4.14	Volts	
	Measured value of Vo- =	4.13	Volts	
	Measured output (Vo+ - Vo-) at zero input pressure =	10	mV	
	Measured output (Vo+ - Vo-) at rated input pressure =	600	mV	
	Untrimmed Span =	590	mV	
	Rated Input Pressure =	50	psi	in K N/m ² = 345 KPa
	Rated Input Pressure =		KPa	in lbs/in ² = 0 psi
	Desired Span =	400	mV	
Output Offset Voltage:				
	Untrimmed Offset Vo+ - Vo- =	10.0	mV	
If Vo+ - Vo- is positive then Rzb is adjusted upwards				
	guess, Rzb =	10560	ohms	
	Rzb to make offset zero =	10560	ohms	gives offset correction = -10.0 mV
	Trimmed Offset =	0.0	mV	
If Vo+ - Vo- is negative then Rzt is adjusted upwards until Vo+ - Vo- is zero				
Span:				
Span can only be adjust smaller from the untrimmed value, so the desired span must be less than measured.				
Calculate Rs to reduce the bridge voltage to make the bridge vlotage smaller by the ratio of desired span/measured span				
	Rst = Rsb =	388	ohms	

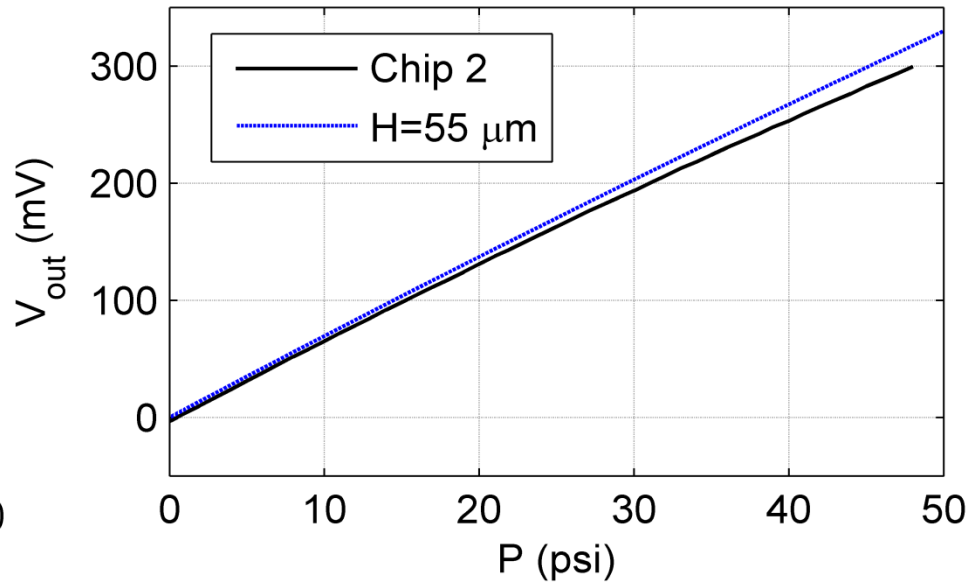
Rochester Institute of
Microelectronic Engi

COMPARISON OF THIN AND THICK DIAPHRAGM

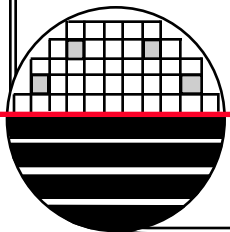
Diffused Resistors



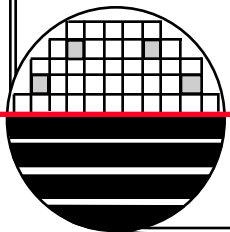
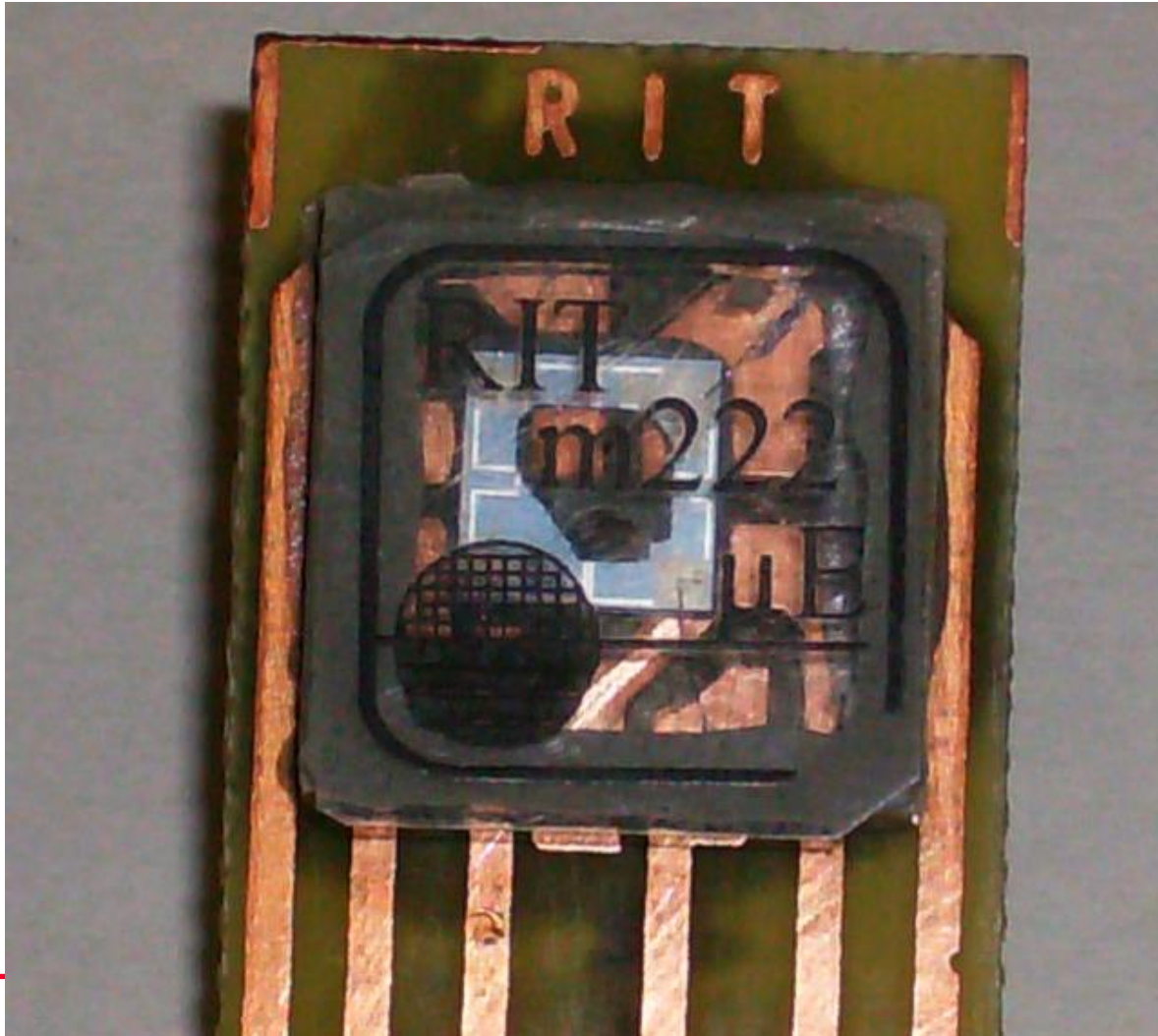
Sensitivity $\sim = 200\text{mV}/12\text{psi}$
 $= 10 \text{ mV/psi}$



Sensitivity $\sim = 100\text{mV}/15\text{psi}$
 $= 6.67 \text{ mV/psi}$



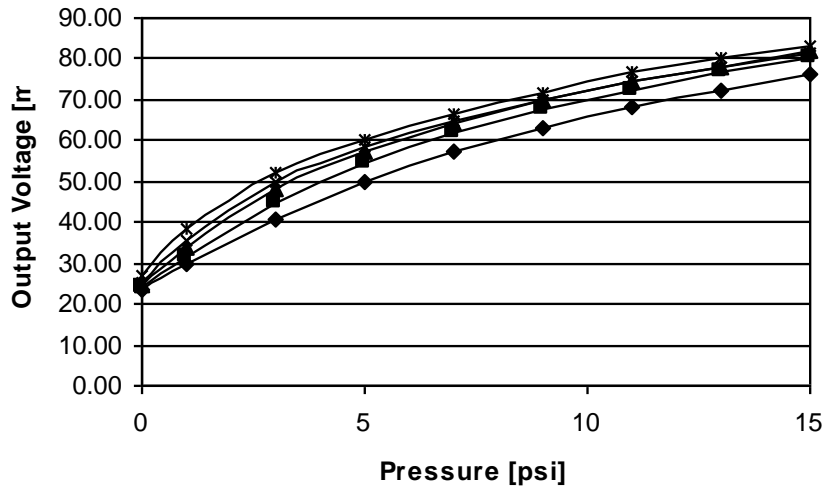
EXCESSIVE PRESSURE



EVALUATION OVER TEMPERATURE

Polysilicon Resistors

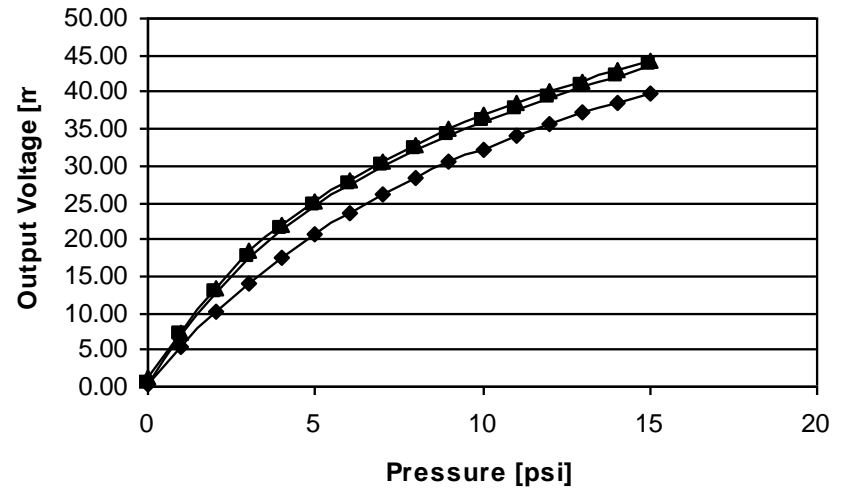
Output Voltage vs. Pressure for Device 2



◆ Temp - 22 C ■ Temp - 50 C ▲ Temp - 70 C
× Temp - 93 C * Temp - 125 C

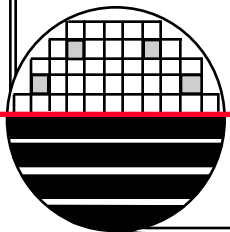
No Compensation

Zero-Span Compensated Pressure Sensor over Temperature

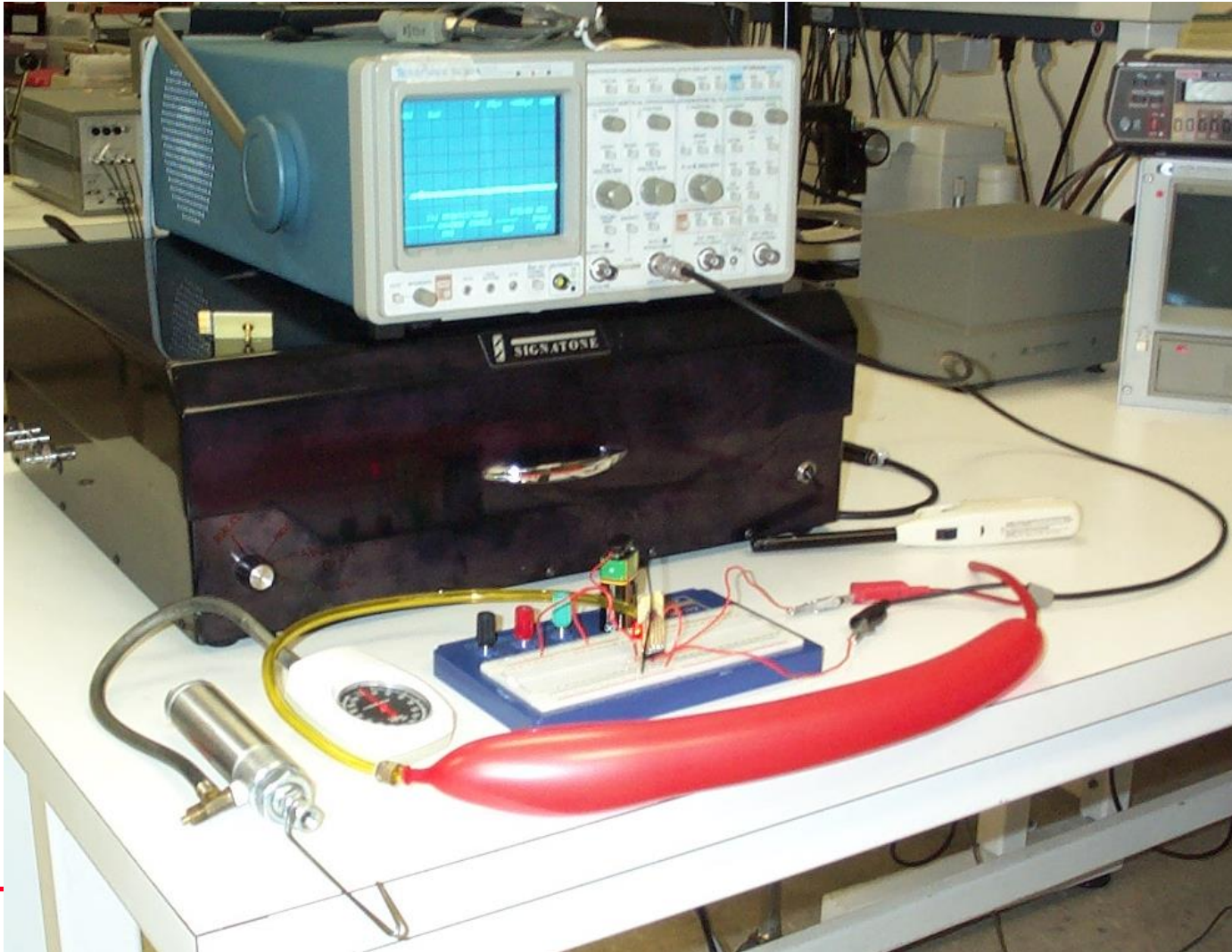


◆ T = 27 C ■ T = 57 C ▲ T = 84 C

Compensated



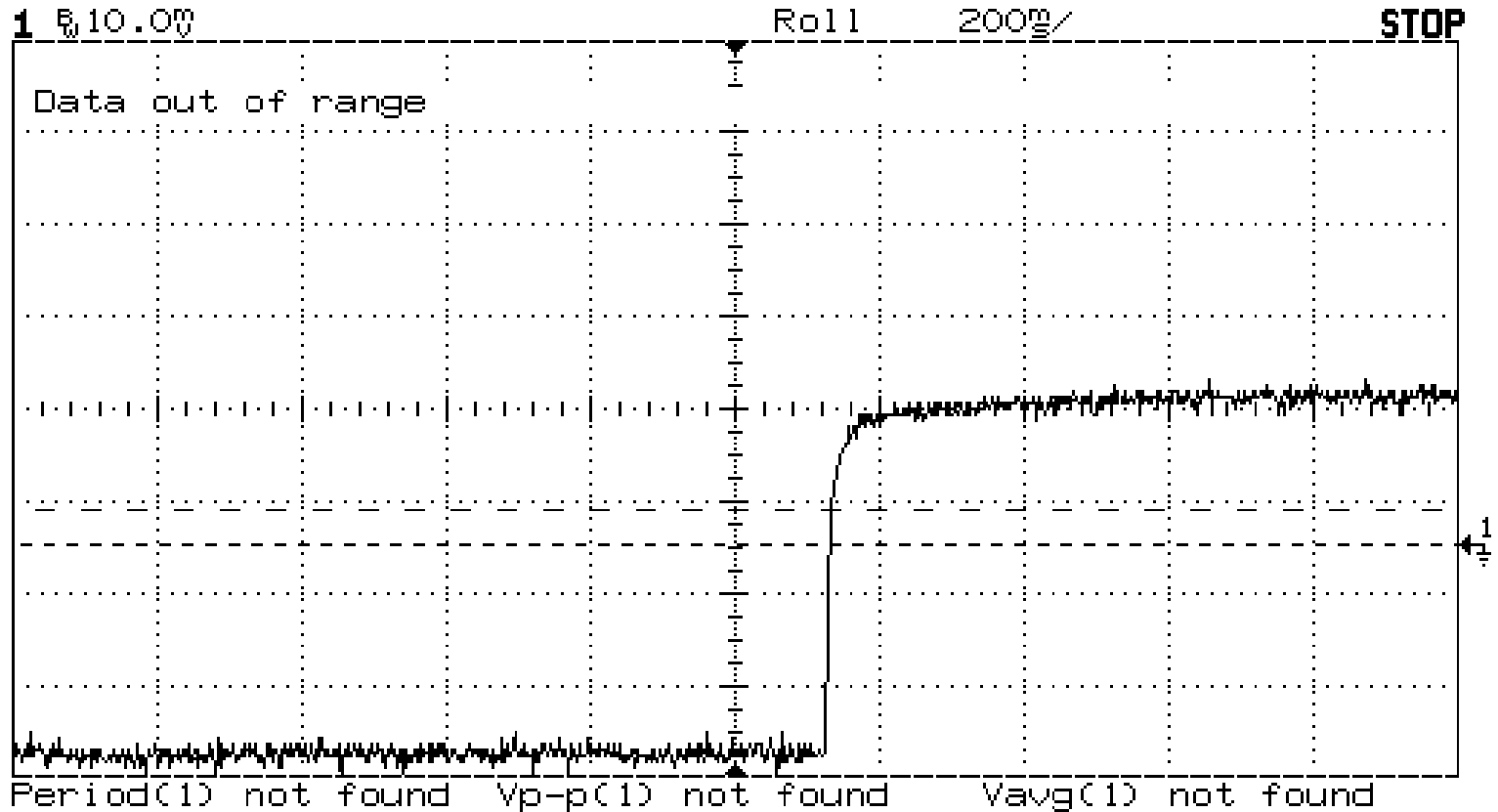
TEST SETUP FOR FREQUENCY MEASUREMENT



BALLOON ABOUT TO POP

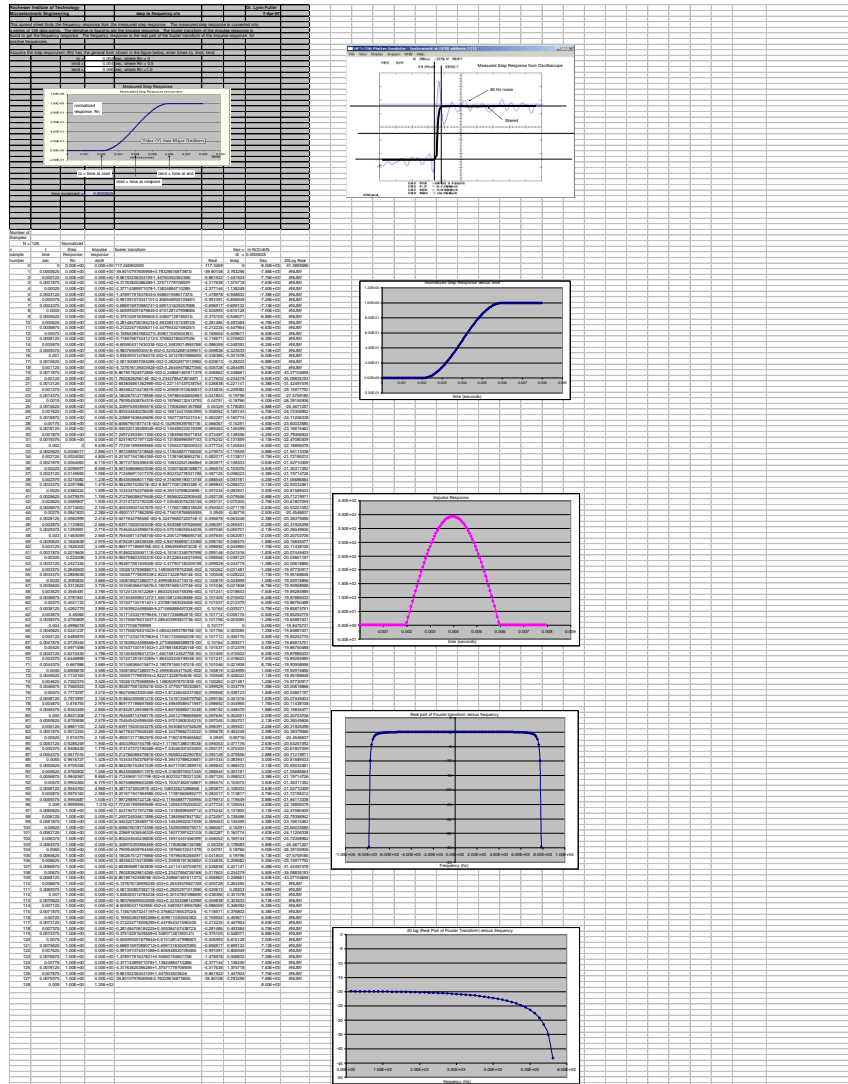


MEASURED STEP RESPONSE



STEP TO IMPULSE TO FREQUENCY RESPONSE

Excel
Spreadsheet



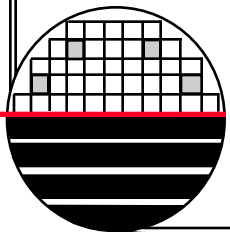
Data

Filtered
Normalized Step
Response

Derivative gives
Impulse Response

Fourier Transform
Gives frequency
response

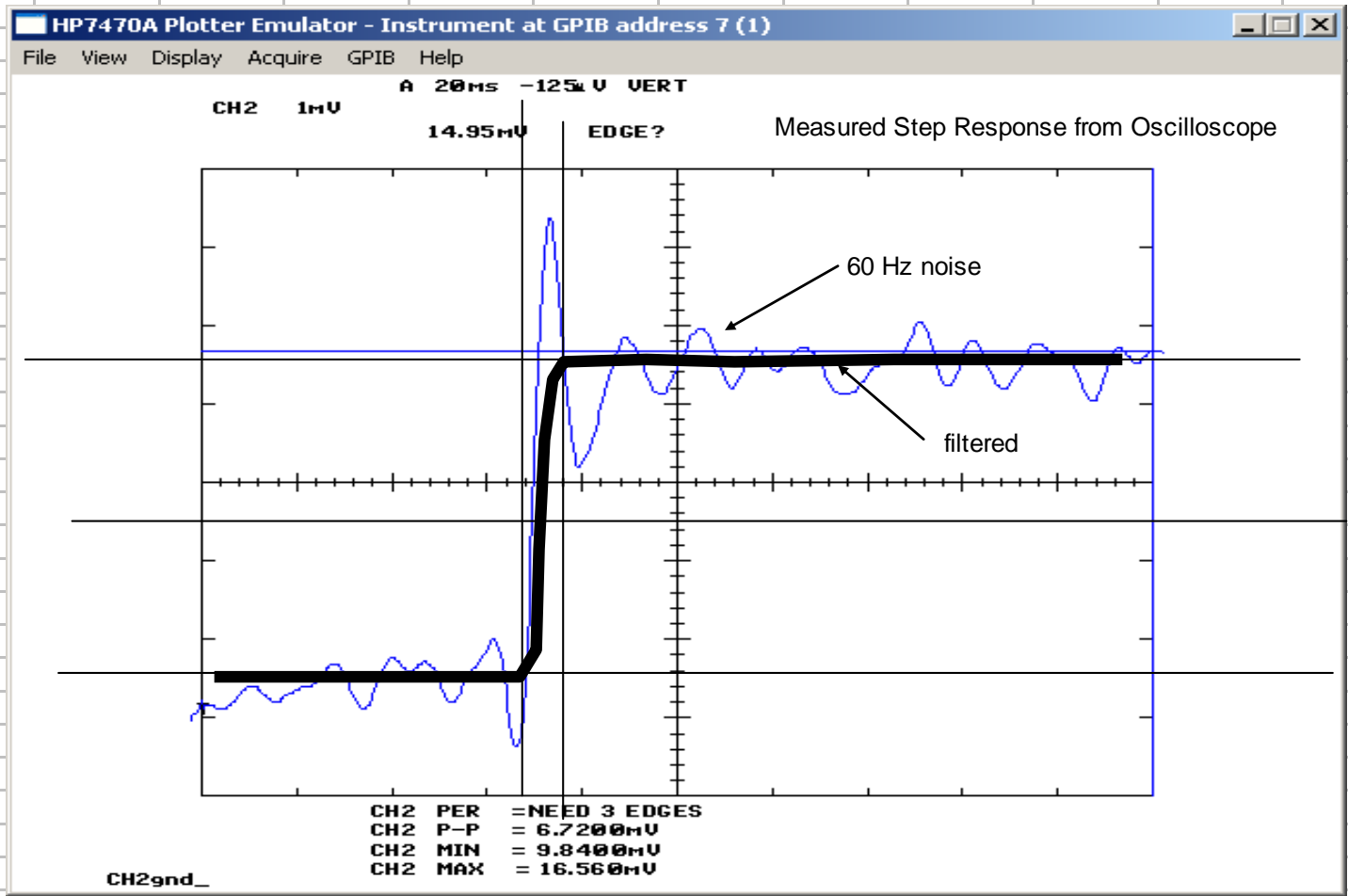
Real Part in dB



STEP TO FREQUENCY.XLS

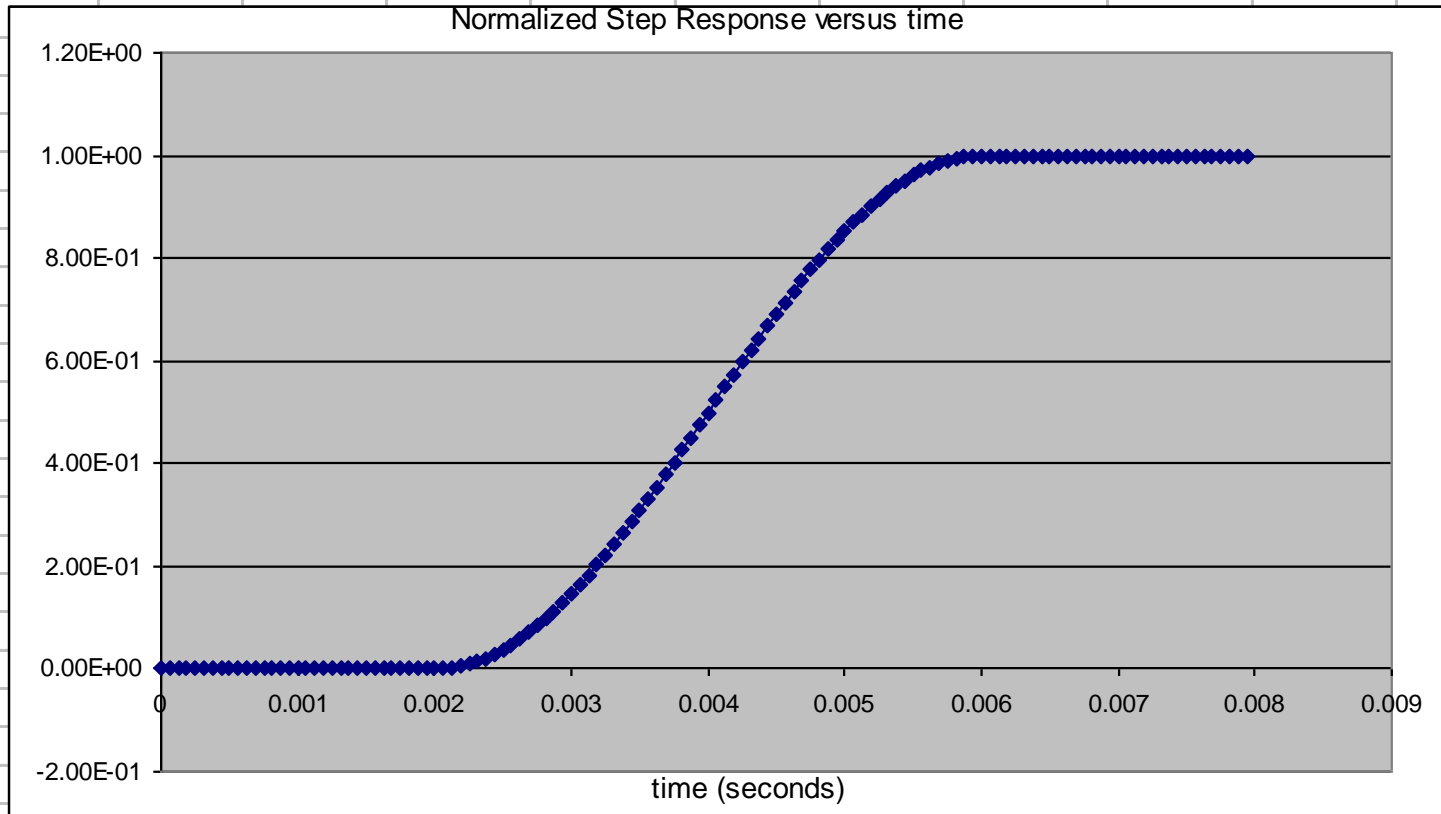
Rochester Institute of Technology				Dr. Lynn Fuller
Microelectronic Engineering		step to frequency.xls		7-Apr-07
<p>This spread sheet finds the frequency response from the measured step response. The measured step response is converted into a series of 128 data points. The derivative is found to get the impulse response. The fourier transform of the impulse response is found to get the frequency response. The frequency response is the real part of the fourier transform of the impulse response for positive frequencies.</p>				
<p>Assume the step responsem (Rn) has the general form shown in the figure below, enter times to, tmid, tend</p>				
	to =	0.002	sec, where Rn = 0	
	tmid =	0.004	sec, where Rn = 0.5	
	tend =	0.006	sec, where Rn =1.0	
Measured Step Response				
	time increment =	0.0000625		

MEASURED STEP RESPONSE

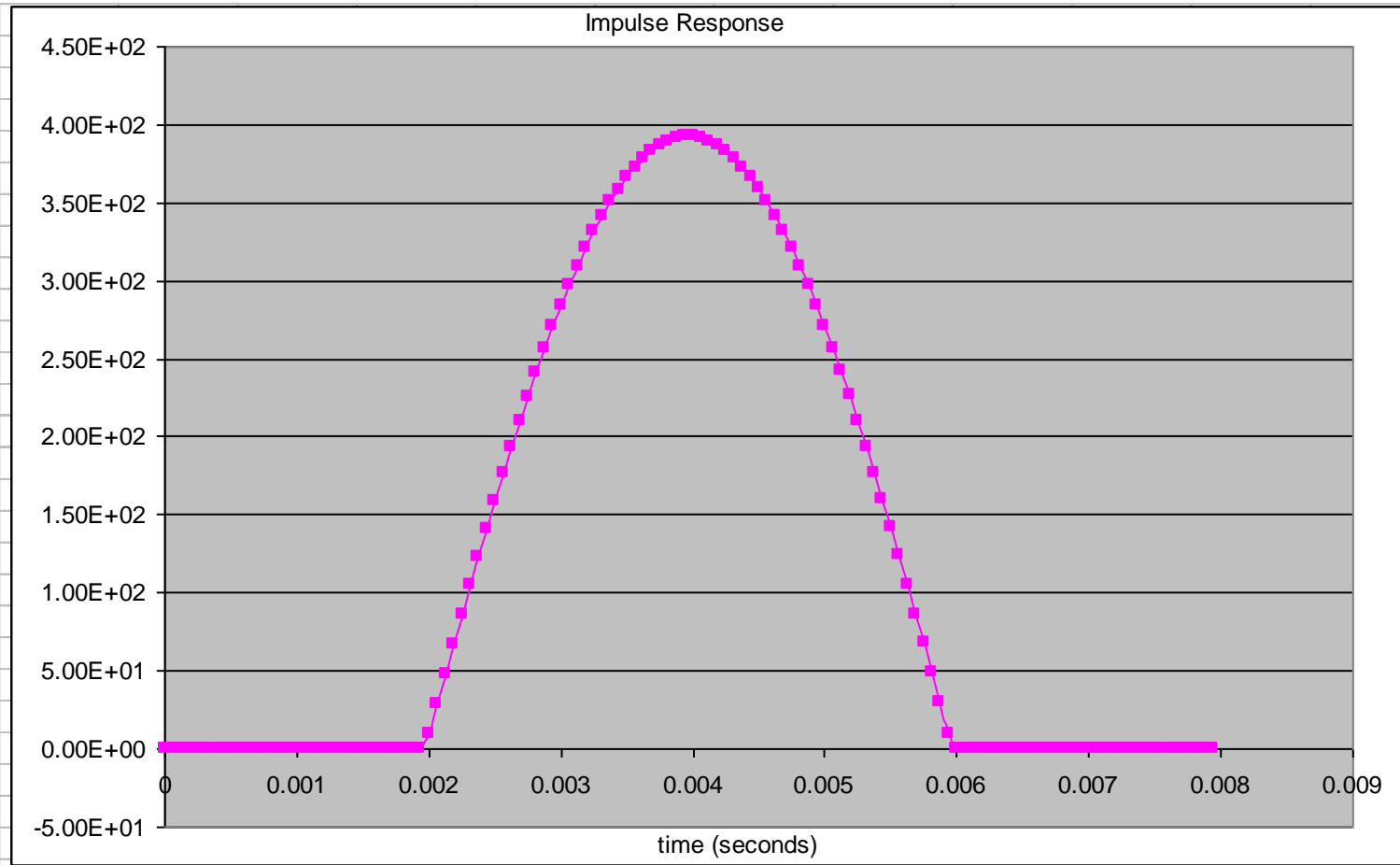


Rochester Institute of Technology
Microelectronic Engineering

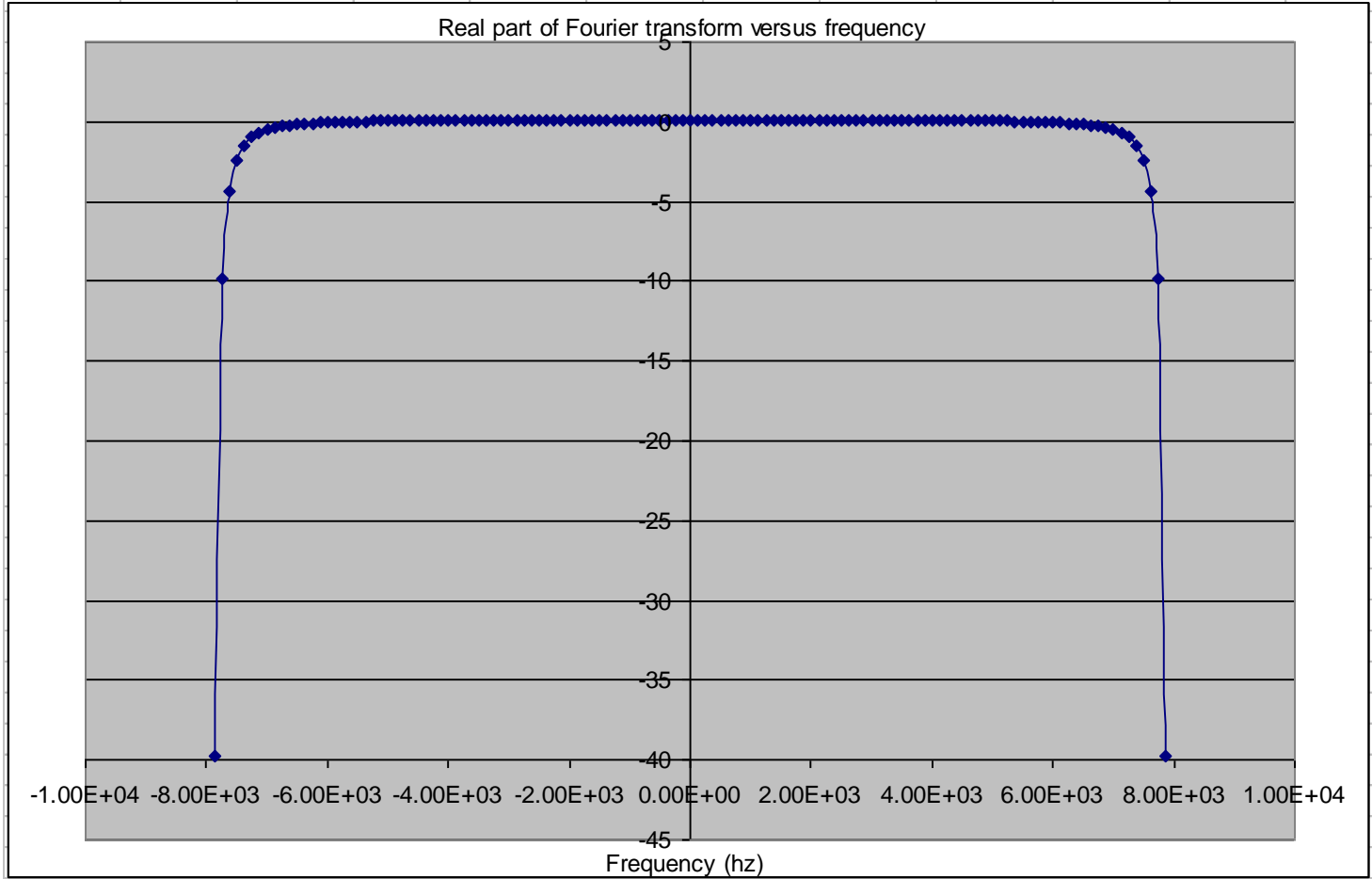
FILTERED NORMALIZED STEP RESPONSE



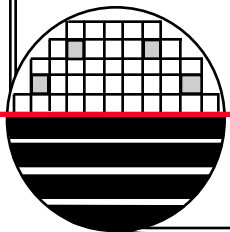
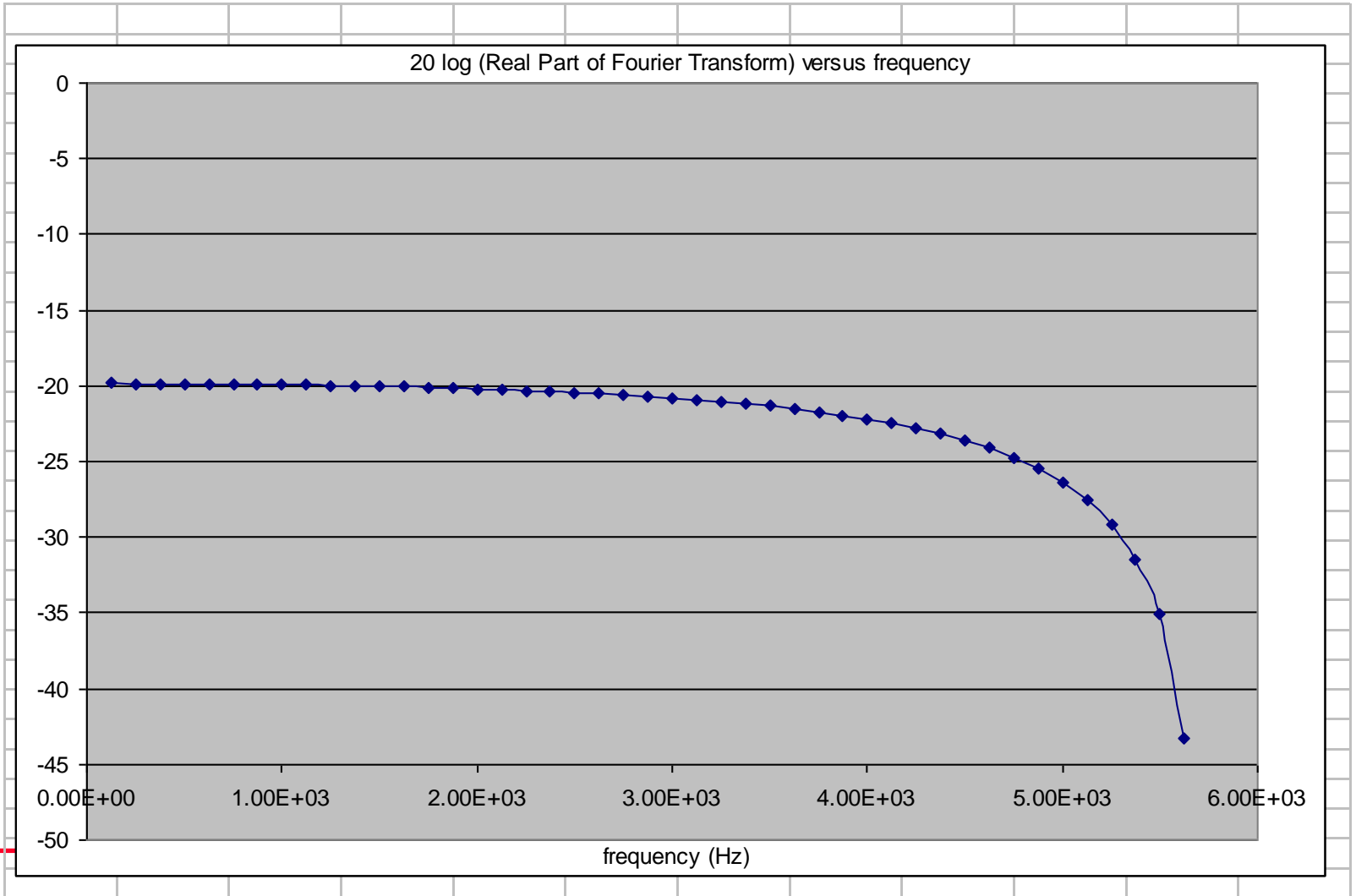
IMPULSE RESPONSE



FOURIER TRANSFORM

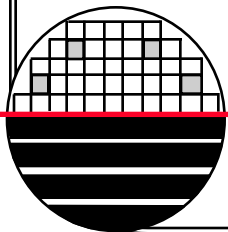


FREQUENCY RESPONSE



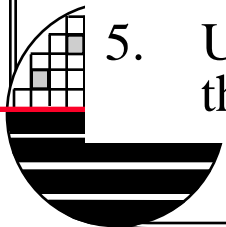
REFERENCES

1. <http://www.lecroy.com/tm/library/LABs/PDF/LAB740.pdf>
2. Microsystem Design, Stephen D, Senturia, Kluwer Academic Publishers, 2000, pg 488-494
3. Micromachined Transducers, McGraw Hill, 1998, Kovacs, pg 253
4. www.youtube.com/watch%3Fv%3DvBN-P5H1-4g



HOMEWORK – PRESSURE SENSOR LAB

1. The example calculations shown on page 4-10 make a lot of assumptions about the fabrication process such as the starting wafer is 500um thick. In fact the starting wafer is thinned and polished to reduce the KOH etch time and the back grinding process is not that exact giving variation of starting wafer thickness between 250 and 350um. List other variables that might vary by more than 10% and discuss how that would effect the sensitivity and offset of the pressure sensor.
2. Discuss the linearity of the pressure sensor. Why do thicker diaphragms give more linear results over a given pressure range. How is the sensitivity affected by thicker diaphragms.
3. Should the pressure be applied to the top or bottom of the sensor? Why?
4. If the compensation network uses laser trimmed resistors which resistor should be trimmed to make the output zero if V_{o+} is +50mV to begin with?
5. Use the bridge balance Excel spread sheet to adjust the zero and span of the pressures sensor on page 20



LAB INSTRUCTORS NOTES

Show MEMS chip

Take Picture

Apply Vacuum

Take Picture

Measure V_{o1} , V_{o2} and $V_{o1}-V_{o2}$ with no pressure

Measure V_{o1} , V_{o2} and $V_{o1}-V_{o2}$ with pressure

For RIT packaged device take data for $V_{o1}-V_{o2}$ versus Pressure

Determine Offset and span

Correct offset and span

Take data for $V_{o1}-V_{o2}$ with corrections.

Take data for Commercial Pressure Sensor

